

UNITED STAT DEPARTMENT OF COMMERCE Patent and Trademark Office Address: COMMISSIONER OF PATENTS AND TRADEMARKS Washington, D.C. 20231

APPLICATION NUMBER	FILING DATE	FIRST NAMED APPLICANT		ATTY, DOCKET NO.
08/578.980 12/2 7/9 5 KAMAKURA			τ	39-5461-0
				EXAMINER
		B5M1/0415		
OBLON SPIVAK MCCLELLAND MAIER & NEUSTADT			-WILLE	
FOURTH FLOOR			ART UNI	A)
1755 JEFFERSON DAVIS HIGHWAY				8
ARLINGTON VA 22202			2508	٠ · · ·
			DATE MAILE	D: 04/15/97

This is a communication from the examiner in charge of your application.

COMM	ISSIGNER OF PATERITS AND TRADEMARING		
	OFFICE ACTI	ON SUMMARY	•
Respon	ensive to communication(s) filed on		
This ac	ction is FINAL.		
Since t	this application is in condition for allowance except for forr dance with the practice under <i>Ex parte Quayle</i> , 1935 D.C.	mal matters, prosecution a 11; 453 O.G. 213.	s to the merits is closed in
whichever i	d statutory period for response to this action is set to expi is longer, from the mailing date of this communication. Fa tition to become abandoned. (35 U.S.C. § 133). Extension	ilure to respond within the	month(s), or thirty days, period for response will cause under the provisions of 37 CFR
Disposition	on of Claims		
Claim((s) 1-10	<u> </u>	is/are pending in the application.
	above, claim(s)		_is/are withdrawn from consideration.
Claim((s)		is/are allowed.
Claim((s)		is/are rejected. is/are objected to.
	(s)		ct to restriction or election requirement.
The dra The pro The sp The sp	ne attached Notice of Draftsperson's Patent Drawing Revierawing(s) filed on	is/are objected to b	oy the Examiner. _is
_		, 	•
Acknow	wledgment is made of a claim for foreign priority under 35 Some* None of the CERTIFIED copies of the		een
☐ re	eceived. ceived in Application No. (Series Code/Serial Number) ceived in this national stage application from the Internation		 2(a)).
*Certifie	ed copies not received:	 	·································
Acknow	wledgment is made of a claim for domestic priority under 3	35 U.S.C. § 119(e).	
Attachmer	nt(s)	-	
☐ Notice	of Reference Cited, PTO-892		18/518980
☐ Inform	nation Disclosure Statement(s), PTO-1449, Paper No(s)		78/ ⁻
☐ Intervi	iew Summary, PTO-413		
Notice	e of Draftperson's Patent Drawing Review, PTO-948		
_	of Informal Patent Application, PTO-152		

Serial Number: 08/578,980 Page 2

Art Unit: 2508

DETAILED ACTION

Claim Rejections - 35 USC § 112

- 1. Claims 8, 9, and 10 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.
- 2. Claims 8, 9, and 10 refer to a dense layer. This term is not defined and does not correspond to the usual meaning of dense. These claims also refer to the lattice constant as being 10⁻². This is not understood since a lattice constant should have dimensions and second, it is in a range which is not physical, no matter what the dimensions.

Claim Rejections - 35 USC § 102

3. Claims 1 and 3 are rejected under 35 U.S.C. 102(b) as being anticipated by Scifres et al. See previous Office Action for a discussion of this rejection.

Claim Rejections - 35 USC § 103

- 4. Claims 2 and 8, 9, and 10, as far as they are understood, are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Inoue et al.
- 5. For a discussion of claim 2 rejection see the previous Office Action. With respect to claims 8, 9, and 10, Scifres et al discusses the basic device structure and refers to the strain layer



Page 3

Serial Number: 08/578,980

Art Unit: 2508

thickness as being approximately 10 nm(column 4, line 47). Scifres et al also discusses the lattice mismatch as being less than or equal to 4%. Inoue et al discusses the defect density as being in the range of 10⁶/cm² which corresponds to a value greater than 10⁴/cm³. It would have been obvious to provide the Scifres et al device with the defect density taught by Inoue et al to improve the defect protection.

- 6. Claims 4, 5, and 6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Sugawara et al. See previous Office Action for a discussion of this rejection.
- 7. Claim 7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Scifres et al in view of Sugawara et al and further in view of Inoue et al. See previous Office Action for a discussion of this rejection.

Response to Arguments

- 8. Applicant's arguments filed 13 January 1997 have been fully considered but they are not persuasive.
- 9. Applicant argues that Scifres et al does not discuss details of defect density, lattice constant or layer thickness. While Scifres et al does not discuss defect density, they do discuss both layer thickness and lattice constant differences as noted above. No discussion of defect density was required before the claims were amended and was therefore not addressed, however, in light of the new claims, it is noted that the question of defect density is addressed by the Inoue et al reference. Applicant also argues that Scifres et al does not show the strain layer as being



Serial Number: 08/578,980

Art Unit: 2508

between the electrode and the hetero-configuration, but applicants' attention is drawn to Figure 2 where the strain layer is shown as being in the middle of the buffer layer and there is still a buffer material layer between the strain layer and the hetero-configuration.

- 10. Applicant argues that claims 3, and 4 have features not discussed by Scifres et al. It is noted that Scifres et al teaches a structure where the clad layers are doped for n- and p-type behavior. While Scifres et al does not specify the doping of the active layer, it is standard practice to leave that layer undoped. Thus the features of these claims were properly addressed in the rejection. Applicant also argues that Scifres et al fails to teach the claimed defect layer either in location or material and the defect is not removed by Inoue et al. Applicants' attention is drawn to the discussion above where the location of the defect layer is exactly as shown in the claims and while Scifres et al does not discuss the defect density this is more than made up by the discussion in Inoue et al where the defect density is shown in great detail. Again, all aspects of the claims were discussed in the references provided.
- 11. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).
- 12. A shortened statutory period for response to this final action is set to expire THREE MONTHS from the date of this action. In the event a first response is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period

Serial Number: 08/578,980

Art Unit: 2508

action.

Page 5

will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event will the statutory period for response expire later than SIX MONTHS from the date of this final

- 13. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Douglas A. Wille whose telephone number is (703) 308-4949.
- 14. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose number is (703) 308-0956.

PRIMARY E

DAW DLW

April 2, 1997